

## Schottky Barrier Diode

VOLTAGE RANGE: 50V PEAK PULSE POWER:200mW

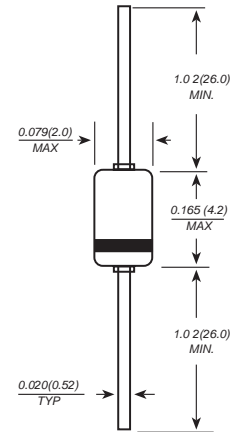
### Features

- For general purpose applications
- These diode is also available in the Mini-MELF case with type designation LL86
- These device are protected by a PN junction guard ring against excessive voltage ,such as electrostatic discharges

### MECHANICAL DATA

- Case: DO-35 Glass
- Polarity: Color band denotes cathode end
- Mounting Position: Any

DO-35(GLASS)



Dimensions in inches and (millimeters)

## MAXIMUM RATINGS AND CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified

Item	Symbol	Unit	Conditions	Max
Continuous reverse voltage	$V_R$	V		50
Forward continuous current	$I_F$	mA	$T_a=25^\circ\text{C}$	200
Repetitive Peak Forward Current	$I_{FSM}$	mA	$t < 1s, \delta < 0.5, T_a=25^\circ\text{C}$	300
Power dissipation	$P_{tot}$	mW	$T_a=65^\circ\text{C}$	200
Maximum junction temperature	$T_j$	°C		125
Ambient operating temperature range	$T_A$	°C		-55 to +125
Storage temperature range	$T_{stg}$	°C		-5 to +150
Junction ambient	$R_{thJA}$	°C/W	On PC board 50mm×50mm×1.6mm	300

## Electrical Specification ( $T_a=25^\circ\text{C}$ unless otherwise specified)

Item	Symbol	Unit	Conditions	Min	Max
Reverse breakdown voltage	$V_{(BR)R}$	V	$I_R=10\mu\text{A}$ (pulsed)	50	
Leakage current	$I_R$	uA	$V_R=25\text{V}$	0.2	0.5
Forward voltage pulse test $t_p < 300\mu\text{s}, s < 2\%$	VF	V	$I_F=0.1\text{mA}$	0.2	0.3
		V	$I_F=1\text{mA}$	0.272	0.380
		V	$I_F=10\text{mA}$	0.365	0.450
		V	$I_F=30\text{mA}$	0.460	0.6
		V	$I_F=100\text{mA}$	0.700	0.9
Capacitance	$C_{tot}$	pF	$V_R=1\text{V}, f=1\text{MHz}$		8
Reverse recovery time	$t_{rr}$	ns	$I_F=I_R=10\text{mA}, I_R=0.1\text{mA}$		5